

#674, Sa-Ri, Seotan-Myeon, Pyeongtaek-Si, Gyeonggi-Do, Korea. 451-852 TEL: +82-31-646-1561 FAX: +82-31-646-1515 E-Mail: jbkim@kostek E-Mail : jbkim@kosteks.com

QUOTATION

We are pleased to offer you the following goods.

Detail information about price, terms and conditions are described hereunder.

Date : Jul 16, 2015 Customer : Chipbond

Product : Plasma Processing System (Rydeen 8200) Quote No. :

A person in charge : Jacob Kim

No	DESCRIPTION	Q'TY	UNIT PRICE	AMOUNT PRICE
1	Plasma Processing System (Rydeen-8200) * Including 2 Process Modules * For 150mm, 200mm & 300mm Wafer	1 system		
2	Option : Dry pump * 1 Dry pump for Process Modules (10,000 L/min) * 1 Dry pump for TM & Load Lock (10,000 L/min)	2 sets		
3	Option : Chiller * Dual channel for 2 Process Modules	1 set		I
	Total Price (Options are not in			

1. Terms & Conditions

1) Delivery date Within 3 months ARO

2) Payment condition

30% By T/T upon receipt of purchase order 60% By T/T before shipment 10% By T/T after completion of performance verification

3) Warranty One(1) year after completion of performance verification

4) Quotation validity term 30 days from the quoted date

US dollars 2. Payment currency

Export standard packing (Vacuum sealed crate) 3. Packing

4. Origin/Shipment from

Jason Bae / President

Kostek Systems, Inc.

	Plasma Processing System, Rydeen 8200			
Date : Jul. 16, 2015 Quote No :				
_	mer : Chipbond			
No	ITEM / DESCRIPTION	Q'ty		
	Geneal Features			
	This system is designed to eliminate scums of PR, PI and BCB in bumping process	1		
	- High performance ICP source with specially designed helical coil	1		
	High density plasma and good ion directionality High accuracy ATM & vacuum robot transfer	1		
	- Field proven RF generator & matching unit	1		
	- Field proven Windows based operating software	1		
		1		
	- Easy to convert wafer size among 150mm, 200mm and 300mm wafers	1		
	- Good process performance			
	Process Performance	-		
	- Etching rate : ≥10,000Å/min @ (our standard recipe of PR removal)	1		
	- Within wafer uniformity : ≤5%	1		
	- Uniformity of wafer to wafer :≤ 3%	1		
	* Calculating method: (max - min) / (2 × Average) × 100%	1		
	* Note: This uniformity should be calculated using average etching rate of each wafer	1		
		1		
	- Particles : ≤ 20ea (@>0.20um)	1		
	- Throughput : ≥ 100 wafers/h (@process time : 30sec)			
	System Configuration			
	1. EFEM	1 set		
	2. Load-lock module	1 set		
	3. Transfer module	1 set		
	4. Process module	2 sets		
	5. ICP RF power generator & matching unit	2 sets		
		2 sets		
	6. Bias RF Power generator & matching unit	1 set		
	7. Power box and controls	1,000		
	8. Operating software	1 set		
1	EFEM	1 set		
	This module transfers wafers from the FOUP to the LL			
	► Compatible for 150mm, 200mm and 300mm wafers	1		
	► High accuracy ATM robot transfer with wafer mapping function for 6" & 8" wafer	1		
	► SEMI standard load-port modules with wafer mapping function for 12" wafer	1		
	▶ Configuration	1		
	ATM robot with mapping function : 1 set	1		
	FFU : 1 set	1		
	Load-port module : 2 sets	1		
	Signal tower : 2 sets	1		
	GUI display unit : 1 set	1		
	UPS : 1 set			
2	Load-lock module	1 set		
	This module is for loading and unloading of wafers between FOUP and TM	1		
	▶ Double stack chamber : upper and lower	1		
	▶ Configuration	1		
	- 2 slots per LL	1		
	- Vacuum and venting unit			
3	Transfer module	1 set		
	This module transfers wafers between LL and PM.			
	▶ High accuracy vacuum robot	1		
	▶ Configuration			
	Transfer chamber : 1 set			
	Vacuum robot : 1 set	1		
	Vacuum and gas unit : 1 set	1		

4	Process module (1 stage/PM)	2 sets
	▶ Inductively Coupled Plasma (ICP) source	
ı	- 'Balanced ICP' plasma source	
ı	- Good uniformity of plasma and gas flow	
ı	- Quartz tube for discharge and clean process	
ı	This module adopts Balanced ICP which achieves good process uniformity.	
ı	▶ Lower electrode unit	
ı	- Ceramic coated Al anodized chuck for wafer backside cooling	
ı	- Ceramic ring for better process uniformity	
ı	► Configuration	
ı	ICP plasma source : 1 set	
ı	Lower electrode : 1 set	
ı	Anodized process chamber : 1 set	
ı	Pressure gauge : 1 set	
ı	Pressure control unit : 1 set	
	Gas box, 5 gases mounted : 1 set	
5	ICP RF power unit	2 sets
ı	ICP RF generator	
ı	- Frequency : 13.56MHz	
ı	- Maximum output : 2kW	
I	- Output impedance : 50 ± 2 Ω	
ı	- Cooling : PCW	
I	Automatic RF matcher	
ı	- Maximum input : 2KW(50 Ω)	
	- Cooling: Forced air	
6	Bias RF power unit	2 sets
ı	Bias RF generator	l
ı	- Frequency : 2.0MHz	l
ı	- Maximum output : 1KW	l
ı	- Cooling : Forced air	l
ı	Automatic RF matcher	l
ı	- Maximum input : 1KW(50 Ω)	l
ı	- Cooling : Forced air	l
7	Controls and power box	1 set
l '	* Industrial computers for CTC,TMC and PMC	1 301
ı	A SO WANTED THE CONTROL OF THE CONTROL OF THE CONTRACT OF THE	l
ı	* 17" touch LCD monitor	l
<u> </u>	* Power distribution unit	
8	Operating software	1 set
ı	* SEMI standard, user friendly, easy to operate	l
ı	* Configurable parameters	l
ı	* CTC/TMC/PMC programs	l
I	* SECS-II/GEM communication and HSMS support (optional)	
	* Windows based software	
9	Wafer Conversion Kit (150mm wafer, 200mm wafer & 300mm wafer)	2 sets
I	Allows 150mm and 200mm wafers to be processed on 300mm load port & process chamber	
I	This option simplifies the wafer size conversion by simply exchanging the kit	
I	End effector of vacuum robot	
I	Ceramic edge ring	
1	Cassette adapter on 300mm load port in case of using 150mm and 200mm wafers	
10	Option ;	1 set
l "	1) Chiller(for cold chuck)	, 361
I	Type : Dual channel for 2 process chambers	
I	Type : Dual channel for 2 process chambers Temperature control	
I	* Control method : PID control	
I	* Control range : 0~40 °C	I
1	* Stability : ±1.0 °C	
1	2) Dry Pump	2 sets
	2 Dry pumps : 10,000L/min	
1	1 dry pump for 2 process chambers : 10,000L/min	
1		
	1 dry pump for load-lock module & transfer module : 10,000L/min	